**Vishay Siliconix** 



### **Power MOSFET**



- Low figure-of-merit Ron x Qa
- 100 % avalanche tested
- · High peak current capability
- dv/dt ruggedness
- Improved T<sub>rr</sub>/Q<sub>rr</sub>
- · Improved gate charge
- · High power dissipations capability
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

<b>TO-247</b>	G
	N-Channel MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V) at T <sub>J</sub> max.	560			
R <sub>DS(on)</sub> (Ω)	$V_{GS} = 10 V$	0.270		
Q <sub>g</sub> max. (nC)	76			
Q <sub>gs</sub> (nC)	21			
Q <sub>gd</sub> (nC)	34			
Configuration	Single			

ORDERING INFORMATION		
Package	TO-247AC	
Lead (Pb)-free	SiHG20N50C-E3	

<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_c = 25 \degree C$ , unless otherwise noted)						
PARAMETER			SYMBOL	LIMIT	UNIT	
Drain-source voltage			V <sub>DS</sub>	500	v	
Gate-source voltage			V <sub>GS</sub>	± 30	v	
Continuous drain current (T <sub>.1</sub> = 150 °C) <sup>a</sup>	V at 10 V	T <sub>C</sub> = 25 °C	1	20		
Continuous drain current $(1) = 150^{\circ}$ C) =	V <sub>GS</sub> at 10 V	T <sub>C</sub> = 100 °C	ID	11	A	
Pulsed drain current <sup>b</sup>	I <sub>DM</sub>	80				
Linear derating factor			1.8	W/°C		
Single pulse avalanche energy <sup>c</sup>		E <sub>AS</sub>	361	mJ		
Maximum power dissipation	PD	250	W			
Reverse diode dV/dt <sup>d</sup>	dV/dt	5	V/ns			
Operating junction and storage temperature range			T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	- °C	
Soldering recommendations (peak temperature)	d For	10 s		300	U	

Notes

a. Limited by maximum junction temperature

b. Repetitive rating; pulse width limited by maximum junction temperature

- c.  $V_{DD}$  = 50 V, starting T<sub>J</sub> = 25 °C, L = 2.5 mH, R<sub>g</sub> = 25  $\Omega$ , I<sub>AS</sub> = 17 A
- d.  $I_{SD} \le 18$  A, di/dt  $\le 380$  A/µs,  $V_{DD} \le V_{DS}$ ,  $T_J \le 150$  °C

e. 1.6 mm from case

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	TYP.	MAX.	UNIT	
Maximum junction-to-ambient	R <sub>thJA</sub>	-	40	°C/W	
Maximum junction-to-case (drain)	R <sub>thJC</sub>	-	0.5	0/11	

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For technical questions, contact: hvm@vishay.com



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Si	H	G20	N5(	C
	-	-		

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0 V, I_D$	= 250 μA	500	-	-	V
V <sub>DS</sub> temperature coefficient	$\Delta V_{DS}/T_{J}$	Reference to	25 °C, I <sub>D</sub> = 1 mA	-	0.7	-	V/°C
Gate-source threshold voltage (N)	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D$	= 250 µA	3.0	-	5.0	V
Gate-source leakage	I <sub>GSS</sub>	$V_{GS} = \pm 30 V$		-	-	± 100	nA
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 500 V,		-	-	25	μA
	USS	$V_{DS} = 400 V,$	$V_{GS} = 0 V, T_J = 125 \ ^{\circ}C$	-	-	250	μΛ
Drain-source on-state resistance	R <sub>DS(on)</sub>	$V_{GS} = 10 \text{ V}$	I <sub>D</sub> = 10 A	-	0.225	0.270	Ω
Forward transconductance	9 <sub>fs</sub>	$V_{DS} = 50 \text{ V}, \text{ I}_{DS}$	<sub>D</sub> = 10 A	-	6.4	-	S
Dynamic							
Input capacitance	C <sub>iss</sub>	$V_{GS} = 0 V_{,}$		-	2451	2942	pF
Output capacitance	C <sub>oss</sub>	$V_{DS} = 25 V$ ,		-	300	360	
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz	f = 1 MHz		26	32	1
Total gate charge	Qg			-	65	76	nC
Gate-source charge	Q <sub>gs</sub>	$V_{GS} = 10 V$	$I_D = 18 \text{ A}, V_{DS} = 400 \text{ V}$	-	21	-	
Gate-drain charge	Q <sub>gd</sub>			-	29	-	
Turn-on delay time	t <sub>d(on)</sub>			-	80	-	
Rise time	t <sub>r</sub>	050.V		-	27	-	- ns
Turn-off delay time	t <sub>d(off)</sub>	$v_{DD} = 250 V,$	$I_D = 18 \text{ A}, \text{ R}_g = 9.1 \Omega$	-	32	-	
Fall time	t <sub>f</sub>			-	44	-	
Gate input resistance	R <sub>g</sub>	f = 1 MHz, op	ben drain	-	1.1	-	Ω
Drain-Source Body Diode Characteristic	s	•					
Continuous source-drain diode current	١ <sub>S</sub>	MOSFET symbol showing the integral reverse p - n junction diode		-	-	20	
Pulsed diode forward current	I <sub>SM</sub>			-	-	80	A
Diode forward voltage	V <sub>SD</sub>	T <sub>J</sub> = 25 °C, I <sub>S</sub>	<sub>s</sub> = 18 A, V <sub>GS</sub> = 0 V	-	-	1.5	V
Reverse recovery time	t <sub>rr</sub>			-	503	-	ns
Reverse recovery charge	Q <sub>rr</sub>	$T_J = 25 \text{ °C, } I_F$	$= I_{S},$	-	6.7	-	μC
Reverse recovery current	I <sub>BBM</sub>	$di/dt = 100 A/\mu s^{V}_{R} = 35 V$		-	30	-	Α





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### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

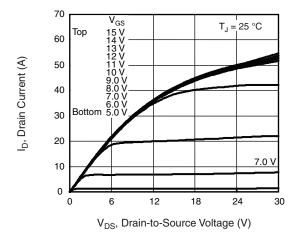


Fig. 1 - Typical Output Characteristics, T<sub>C</sub> = 25 °C

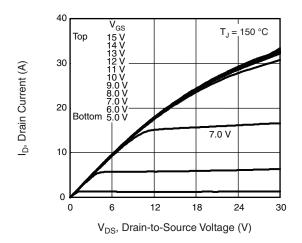
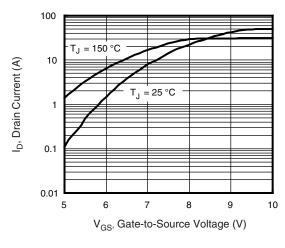


Fig. 2 - Typical Output Characteristics,  $T_C = 150$  °C





R<sub>DS(on)</sub>, Drain-to-Source On Resistance З = 17 A n 2.5 2 (Normalized) 1.5 V<sub>GS</sub> = 10 V 1 0.5 0 - 60 - 40 20 0 20 40 60 80 100 120 140 160 T<sub>.I</sub>, Junction Temperature (°C)

Fig. 4 - Normalized On-Resistance vs. Temperature

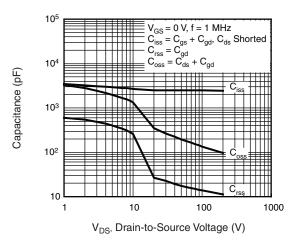


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

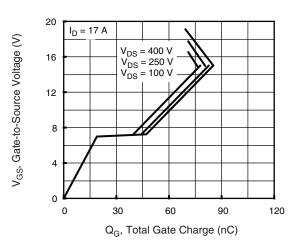


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

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100 µs

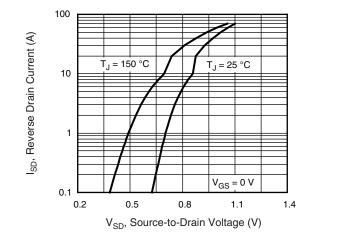
1 ms

10 ms

1000

10 000

11







V<sub>DS</sub>, Drain-to-Source Voltage (V)

1000

100

10

1

0.1 L 10

I<sub>D</sub>, Drain Current (A)

Operation in this area limited

= 25 °C = 150 °C

11111

100

Single Pulse

ТJ

by R<sub>DS(on)</sub>

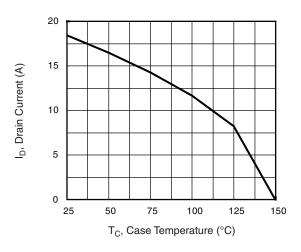
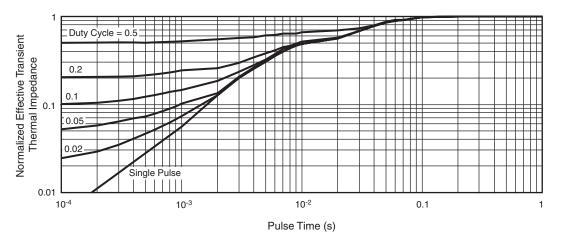
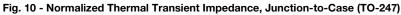


Fig. 9 - Maximum Drain Current vs. Case Temperature





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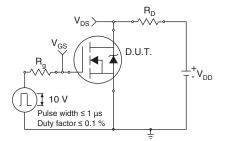


Fig. 11 - Switching Time Test Circuit

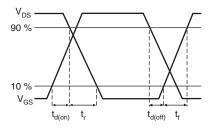


Fig. 12 - Switching Time Waveforms

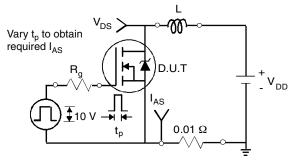


Fig. 13 - Unclamped Inductive Test Circuit

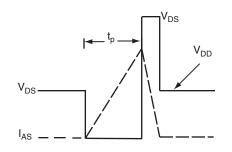
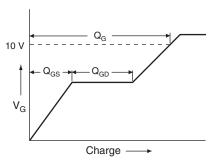


Fig. 14 - Unclamped Inductive Waveforms



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Fig. 15 - Basic Gate Charge Waveform

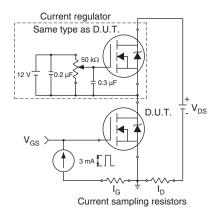


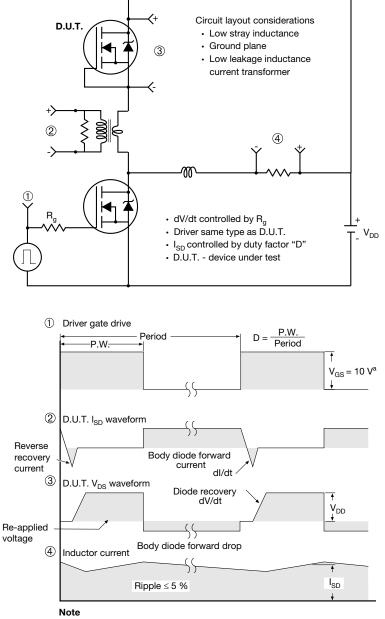
Fig. 16 - Gate Charge Test Circuit

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#### Peak Diode Recovery dV/dt Test Circuit



a.  $V_{GS} = 5$  V for logic level devices

Fig. 17 - For N-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="http://www.vishay.com/ppg?91382">www.vishay.com/ppg?91382</a>.

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## TO-247AC (High Voltage)

### VERSION 1: FACILITY CODE = 9





Section C--C, D--D, E--E

1	 \

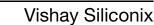
	MILLIN	MILLIMETERS		
DIM.	MIN.	MAX.	NOTES	
А	4.83	5.21		
A1	2.29	2.55		
A2	1.50	2.49		
b	1.12	1.33		
b1	1.12	1.28		
b2	1.91	2.39	6	
b3	1.91	2.34		
b4	2.87	3.22	6, 8	
b5	2.87	3.18		
С	0.55	0.69	6	
c1	0.55	0.65		
D	20.40	20.70	4	

	MILLIN		
DIM.	MIN.	MAX.	NOTES
D1	16.25	16.85	5
D2	0.56	0.76	
E	15.50	15.87	4
E1	13.46	14.16	5
E2	4.52	5.49	3
е	5.44	BSC	
L	14.90	15.40	
L1	3.96	4.16	6
ØΡ	3.56	3.65	7
Ø P1	7.19		
Q	5.31	5.69	
S	5.54	5.74	

#### Notes

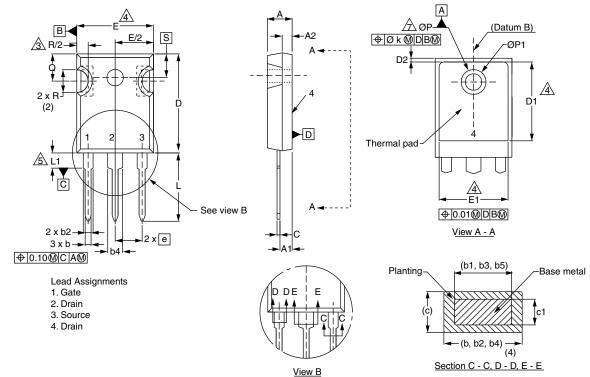
- <sup>(1)</sup> Package reference: JEDEC<sup>®</sup> TO247, variation AC
- (2) All dimensions are in mm
- <sup>(3)</sup> Slot required, notch may be rounded
- <sup>(4)</sup> Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- <sup>(5)</sup> Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- (7) Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition

Revision: 19-Oct-2020





#### VERSION 2: FACILITY CODE = Y



	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
А	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
С	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

	MILLIN	MILLIMETERS	
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
E	15.29	15.87	
E1	13.72	-	
е	5.46 BSC		
Øk	0.254		
L	14.20	16.25	
L1	3.71	4.29	
ØР	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51	5.51 BSC	

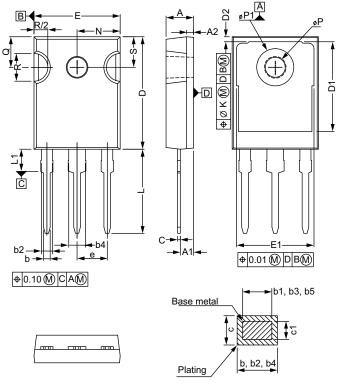
#### Notes

- <sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5M-1994
- <sup>(2)</sup> Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- <sup>(4)</sup> Thermal pad contour optional with dimensions D1 and E1
- <sup>(5)</sup> Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- <sup>(7)</sup> Outline conforms to JEDEC outline TO-247 with exception of dimension c



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### VERSION 3: FACILITY CODE = N



DIM.	MILLIMETERS			MILLIMETERS	
	MIN.	MAX.	DIM.	MIN.	MAX.
А	4.65	5.31	D2	0.51	1.35
A1	2.21	2.59	E	15.29	15.87
A2	1.17	1.37	E1	13.46	-
b	0.99	1.40	e	5.46 BSC	
b1	0.99	1.35	k	0.254	
b2	1.65	2.39	L	14.20	16.10
b3	1.65	2.34	L1	3.71	4.29
b4	2.59	3.43	N	7.62 BSC	
b5	2.59	3.38	Р	3.56	3.66
С	0.38	0.89	P1	-	7.39
c1	0.38	0.84	Q	5.31	5.69
D	19.71	20.70	R	4.52	5.49
D1	13.08	-	S	5.51 BSC	

Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5M-1994

<sup>(2)</sup> Contour of slot optional

<sup>(3)</sup> Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

<sup>(4)</sup> Thermal pad contour optional with dimensions D1 and E1

<sup>(5)</sup> Lead finish uncontrolled in L1

<sup>(6)</sup> Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

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